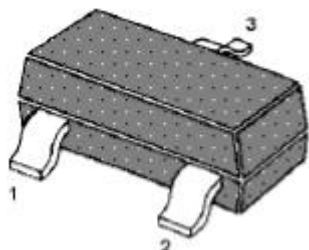


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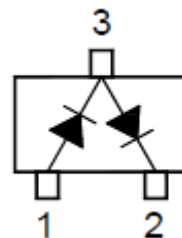
BAV99

Silicon Epitaxial Planar Switching Diode

Fast switching in thick and thin-film circuits diode



Marking Code: A7
SOT-23 Plastic Package



Absolute Maximum Ratings (Ta = 25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current (Double Diode Loaded)	I_F	125	mA
Continuous Forward Current (Single Diode Loaded)	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current		0.5	
	at t = 1 s		
	at t = 1 ms	1	A
	at t = 1 μ s	4.5	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

Characteristics at Ta = 25°C

PARAMETER	SYMBOL	MAX.	UNIT
Forward Voltage			
at $I_F = 1$ mA		0.715	
at $I_F = 10$ mA	V_F	0.855	V
at $I_F = 50$ mA		1	
at $I_F = 150$ mA		1.25	
Reverse Current			
at $V_R = 25$ V		30	nA
at $V_R = 75$ V	I_R	1	μ A
at $V_R = 25$ V, $T_J = 150^\circ\text{C}$		30	μ A
at $V_R = 75$ V, $T_J = 150^\circ\text{C}$		50	μ A
Diode Capacitance			
at $V_R = 0$, $f = 1$ MHz	C_d	1.5	pF
Reverse Recovery Time			
at $I_F = I_R = 10$ mA, $I_R = 1$ mA, $R_L = 100 \Omega$	t_{rr}	4	ns

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BAV99

Silicon Epitaxial Planar
Switching Diode

RATINGS AND CHARACTERISTIC CURVES BAV99

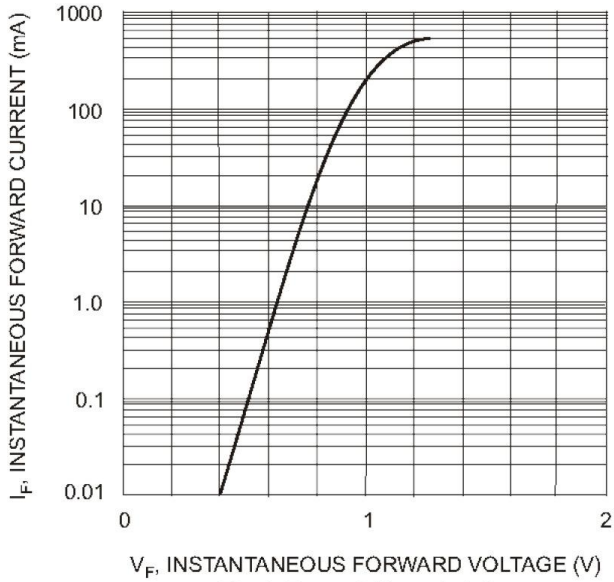


Fig. 1 Forward Characteristics

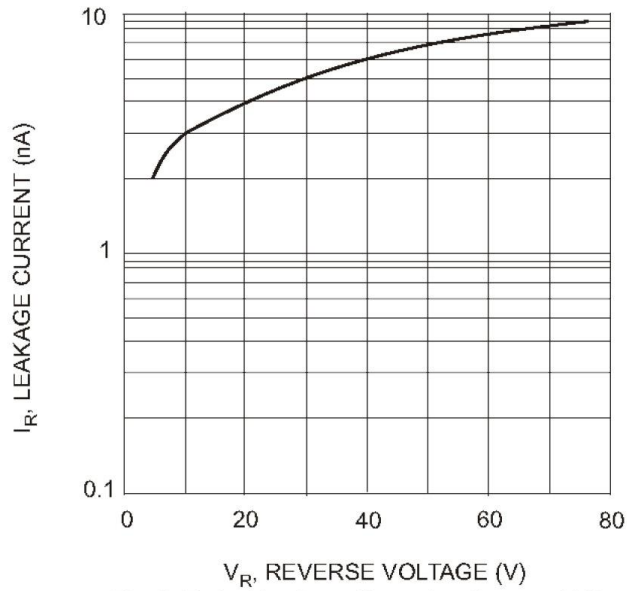


Fig. 2 Typical Leakage Current vs Reverse Voltage

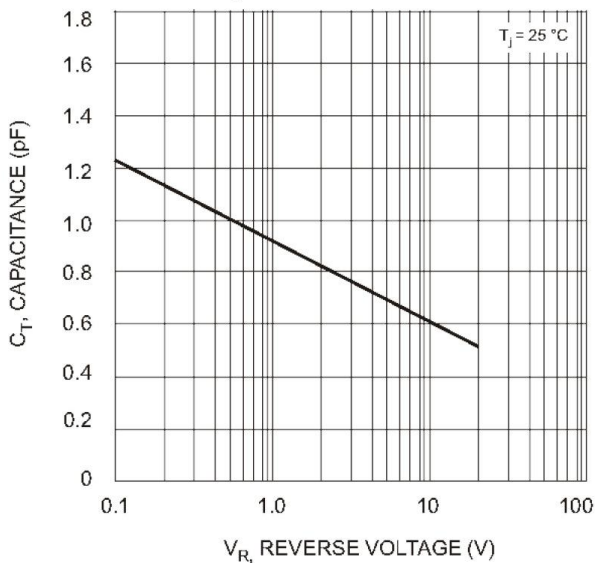


Fig. 3 Typical Total Capacitance vs Reverse Voltage

Note: Specifications are subject to change without notice.

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